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PSMNR70-40SSH

N-channel 40 V, 0.7 mΩ, 425 Amps continuous, standard level MOSFET in LFPAK88 using NextPowerS3 Technology

19 June 2019 Product data sheet

1. General description

425 Amp continuous current, standard level gate drive, N-channel enhancement mode MOSFET in LFPAK88 package. NextPowerS3 family using Nexperia's unique "SchottkyPlus" technology delivers high efficiency and low spiking performance usually associated with MOSFETs with an integrated Schottky or Schottky-like diode but without problematic high leakage current. NextPowerS3 is particularly suited to high efficiency applications at high switching frequencies, and also safe and reliable switching at high load-current.

2. Features and benefits

- 425 Amp continuous current capability
- LFPAK88 (8 x 8 mm) LFPAK-style low-stress exposed lead-frame for ultimate reliability, optimum soldering and easy solder-joint inspection
- Copper-clip and solder die attach for low package inductance and resistance, and high I_D (max) rating
- Ideal replacement for D2PAK and 10 x 12 mm leadless package types
- Qualified to 175 °C
- Meets UL2595 requirements for creepage and clearance
- Avalanche rated, 100 % tested
- Low Q_G, Q_{GD} and Q_{OSS} for high efficiency, especially at higher switching frequencies
- Superfast switching with soft body-diode recovery for low-spiking and ringing, recommended for low EMI designs
- Unique "SchottkyPlus" technology for Schottky-like switching performance and low I_{DSS} leakage
- Narrow $V_{GS(th)}$ rating for easy paralleling and improved current sharing
- Very strong linear-mode / safe operating area characteristics for safe and reliable switching at high-current conditions

3. Applications

- Brushless DC motor control
- Synchronous rectifier in high-power AC-DC applications, e.g. server power supplies
- Battery protection
- eFuse and load switch
- Hotswap / in-rush current management

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T_j ≤ 175 °C		-	-	40	V
I_D	drain current	V_{GS} = 10 V; T_{mb} = 25 °C; Fig. 2	[1]	-	-	425	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 1		-	-	375	W

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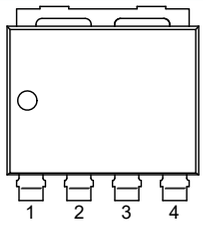
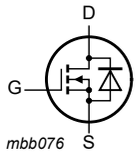
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Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5		-	0.35	0.4	K/W
Static characteristics							
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 11		0.43	0.62	0.7	mΩ
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	I_D = 25 A; V_{DS} = 32 V; V_{GS} = 10 V; Fig. 13; Fig. 14		-	144	202	nC
Q_{GD}	gate-drain charge			-	25	50	nC
Source-drain diode							
Q_r	recovered charge	I_S = 25 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 20 V; Fig. 17	[2]	-	74	-	nC

[1] 425A. Continuous current has been successfully demonstrated during application. Practically, the current will be limited by the PCB, thermal design and operating temperature.
[2] includes capacitive recovery

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 LFPAK88 (SOT1235)	
2	S	source		
3	S	source		
4	S	source		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMNR70-40SSH	LFPAK88	plastic, single-ended surface-mounted package (LFPAK88); 4 leads; 2 mm pitch; 8 mm x 8 mm x 1.6 mm body	SOT1235

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T_j ≤ 175 °C		-	40	V
V_{DSM}	peak drain-source voltage	t_p ≤ 20 ns; f ≤ 500 kHz; $E_{DS(AL)}$ ≤ 200 nJ; pulsed		-	45	V
V_{DGR}	drain-gate voltage	25 °C ≤ T_j ≤ 175 °C; R_{GS} = 20 kΩ		-	40	V
V_{GS}	gate-source voltage			-20	20	V
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 1		-	375	W

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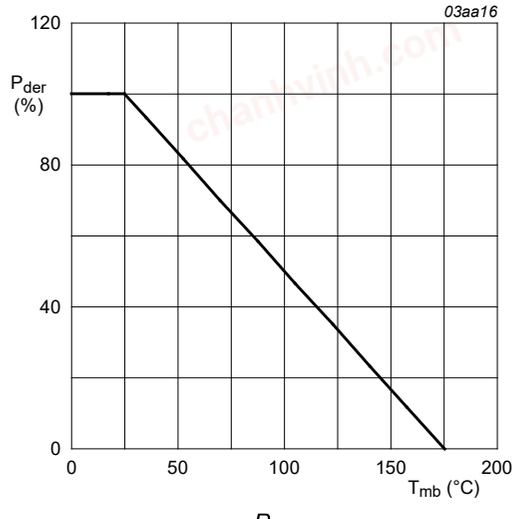
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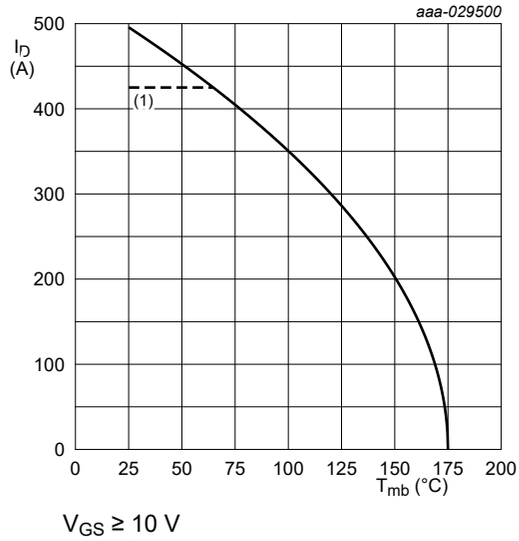
Symbol	Parameter	Conditions		Min	Max	Unit
I_D	drain current	V_{GS} = 10 V; T_{mb} = 25 °C; Fig. 2	[1]	-	425	A
		V_{GS} = 10 V; T_{mb} = 100 °C; Fig. 2		-	350	A
I_{DM}	peak drain current	pulsed; $t_p \leq$ 10 µs; T_{mb} = 25 °C; Fig. 3		-	1983	A
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-drain diode						
I_S	source current	T_{mb} = 25 °C	[2]	-	500	A
I_{SM}	peak source current	pulsed; $t_p \leq$ 10 µs; T_{mb} = 25 °C		-	1983	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	I_D = 120 A; $V_{sup} \leq$ 40 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4		-	940	mJ
I_{AS}	non-repetitive avalanche current	V_{sup} = 40 V; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; R_{GS} = 50 Ω	[3]	-	294	A

[1] 425A. Continuous current has been successfully demonstrated during application. Practically, the current will be limited by the PCB, thermal design and operating temperature.
[2] 500A. Continuous current has been successfully demonstrated during application. Practically, the current will be limited by the PCB, thermal design and operating temperature.
[3] Protected by 100% test



$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\ \%$$

Fig. 1. Normalized total power dissipation as a function of mounting base temperature

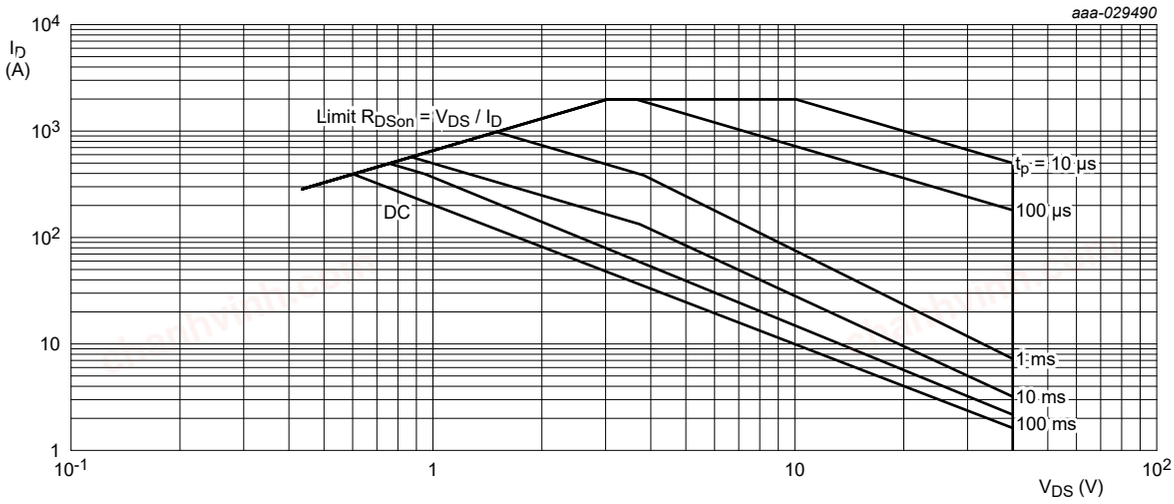


$V_{GS} \geq$ 10 V
(1) 425A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

Fig. 2. Continuous drain current as a function of mounting base temperature

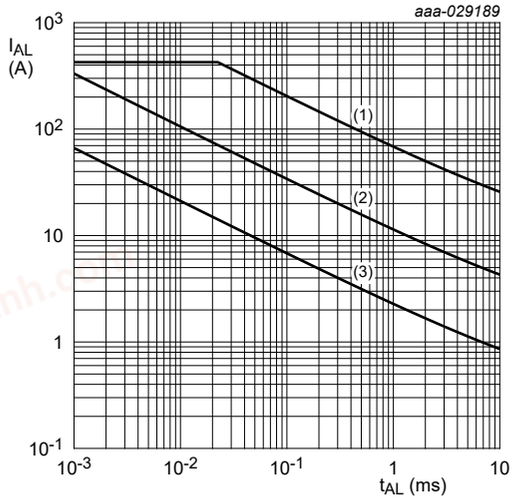
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T_{mb} = 25 °C; I_{DM} is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



(1) $T_{j\ (init)}$ = 25 °C; (2) $T_{j\ (init)}$ = 150 °C; (3) Repetitive Avalanche

Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5		-	0.35	0.4	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Fig. 6		-	35	-	K/W
		Fig. 7		-	70	-	K/W

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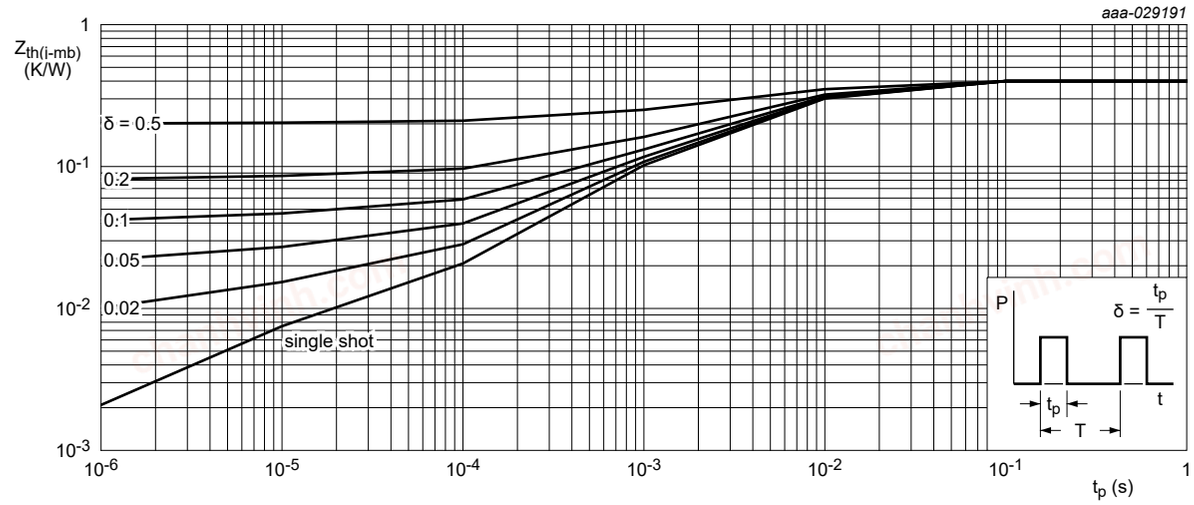
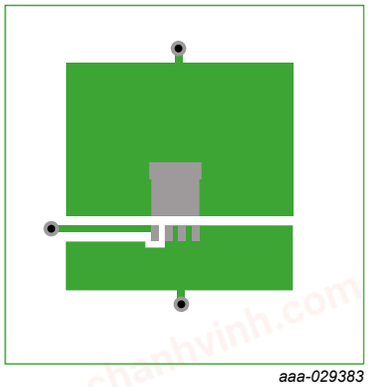
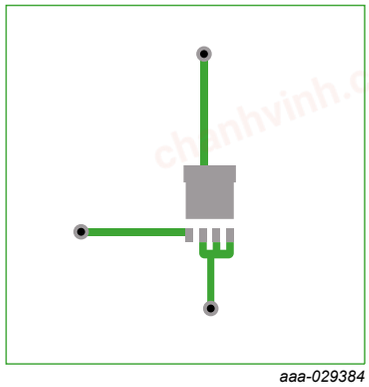


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration



Copper square 25.4 mm x 25.4 mm; 70 µm thick on FR4 board

Fig. 6. PCB layout for resistance from junction to ambient



70 µm thick copper on FR4 board

Fig. 7. PCB layout with minimum footprint for thermal resistance from junction to ambient

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		40	43	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C		36	40	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS}=V_{GS}; T_j = 25 °C		2.4	3	3.6	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	25 °C ≤ T_j ≤ 175 °C		-	-8.2	-	mV/K
I_{DSS}	drain leakage current	V_{DS} = 32 V; V_{GS} = 0 V; T_j = 25 °C		-	-	1.6	µA
		V_{DS} = 32 V; V_{GS} = 0 V; T_j = 175 °C		-	264	-	µA
I_{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C		-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C		-	2	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 11		0.43	0.62	0.7	mΩ

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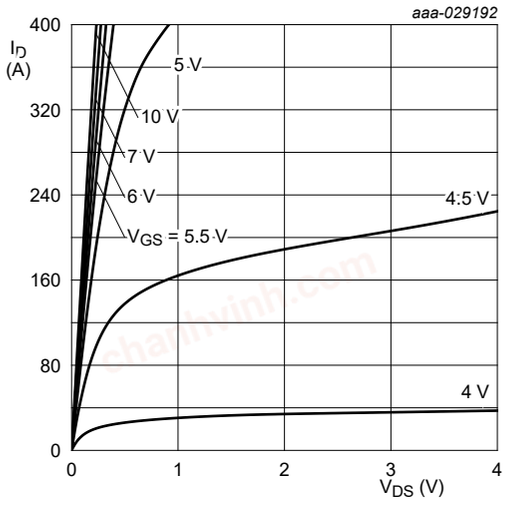
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
		V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; Fig. 12		0.85	1.23	1.53	mΩ
R_G	gate resistance	f = 1 MHz; T_j = 25 °C		0.5	1.2	3	Ω
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	I_D = 25 A; V_{DS} = 32 V; V_{GS} = 10 V; Fig. 13; Fig. 14		-	144	202	nC
		I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V		-	72	-	nC
Q_{GS}	gate-source charge	I_D = 25 A; V_{DS} = 32 V; V_{GS} = 10 V; Fig. 13; Fig. 14		-	40	60	nC
$Q_{GS(th)}$	pre-threshold gate-source charge			-	29	43	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge			-	11	17	nC
Q_{GD}	gate-drain charge			-	25	50	nC
$V_{GS(pl)}$	gate-source plateau voltage	I_D = 25 A; V_{DS} = 32 V; Fig. 13; Fig. 14		-	4.1	-	V
C_{iss}	input capacitance	V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; Fig. 15		-	11228	15719	pF
C_{oss}	output capacitance			-	2363	3308	pF
C_{rss}	reverse transfer capacitance			-	415	913	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 30 V; R_L = 1.2 Ω; V_{GS} = 10 V; $R_{G(ext)}$ = 5 Ω		-	35	-	ns
t_r	rise time			-	30	-	ns
$t_{d(off)}$	turn-off delay time			-	94	-	ns
t_f	fall time			-	41	-	ns
Q_{oss}	output charge	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz; T_j = 25 °C		-	102	-	nC
Source-drain diode							
V_{SD}	source-drain voltage	I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C; Fig. 16		-	0.75	1	V
t_{rr}	reverse recovery time	I_S = 25 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 20 V; Fig. 17		-	53	-	ns
Q_r	recovered charge		[1]	-	74	-	nC
t_a	reverse recovery rise time			-	30	-	ns
t_b	reverse recovery fall time			-	23	-	ns

[1] includes capacitive recovery

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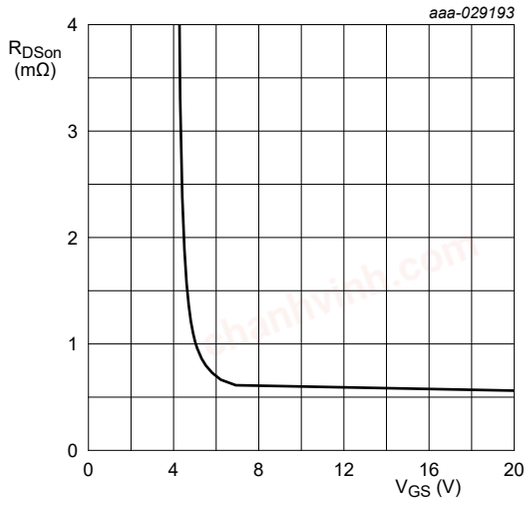
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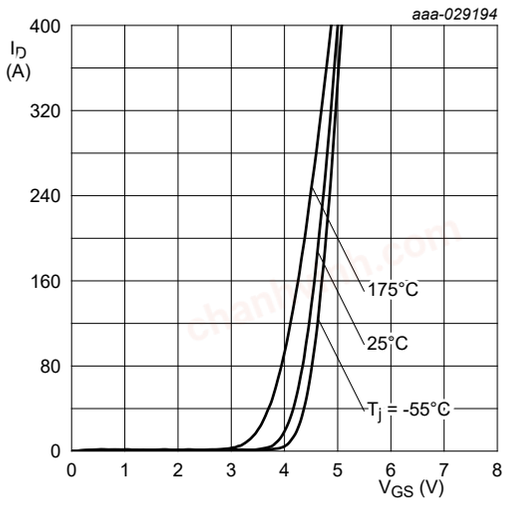
T_j = 25 °C

Fig. 8. Output characteristics; drain current as a function of drain-source voltage; typical values



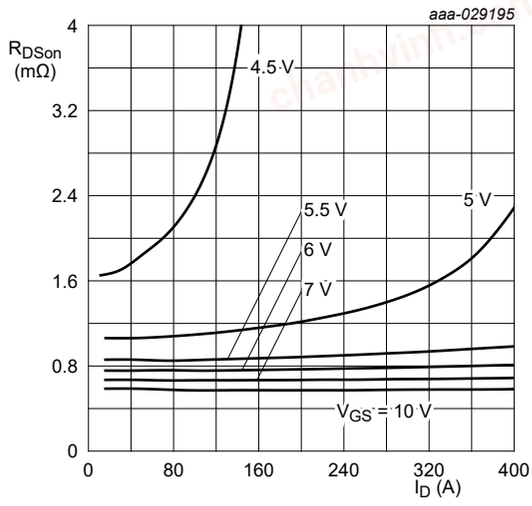
T_j = 25 °C; I_D = 25 A

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



V_{DS} = 8 V

Fig. 10. Transfer characteristics; drain current as a function of gate-source voltage; typical values



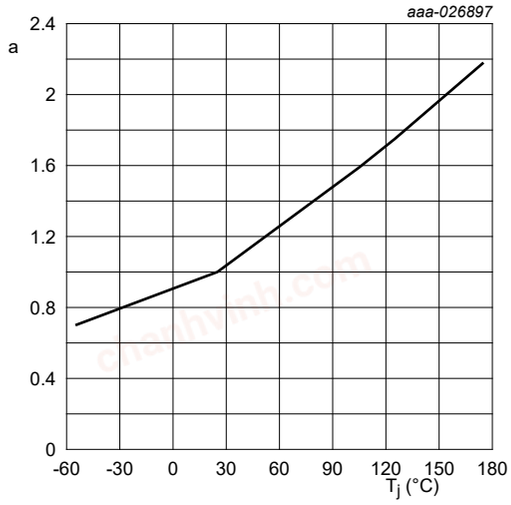
T_j = 25 °C

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

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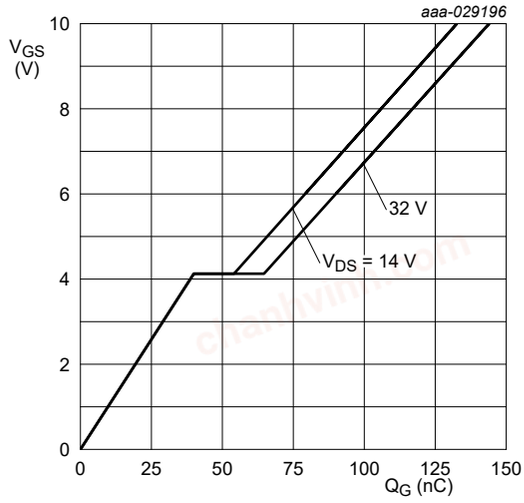
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$$a = \frac{R_{DSon}}{R_{DSon}(25°C)}$$

Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature



T_j = 25 °C; I_D = 25 A

Fig. 13. Gate-source voltage as a function of gate charge; typical values

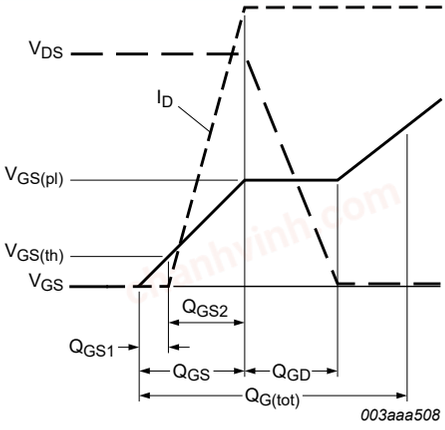
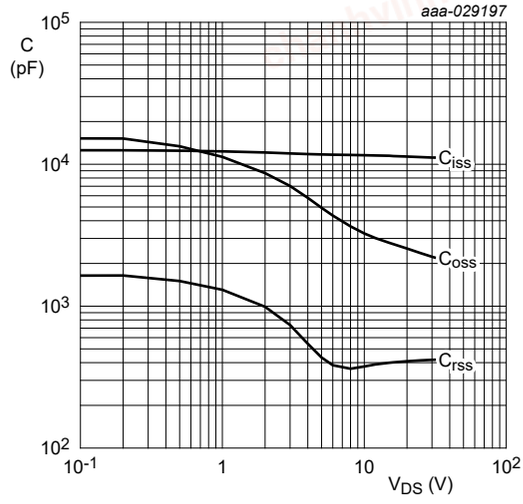


Fig. 14. Gate charge waveform definitions



V_{GS} = 0 V; f = 1 MHz

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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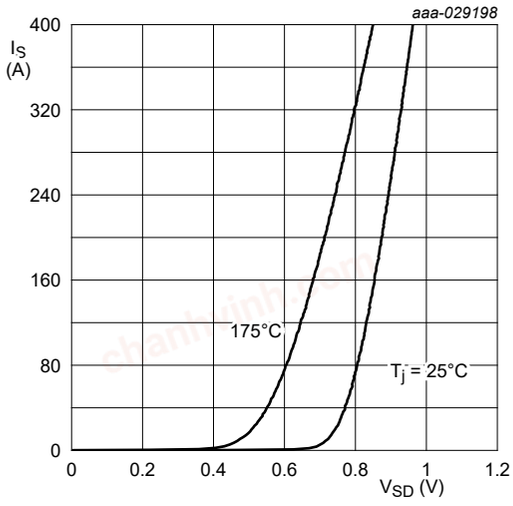


Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

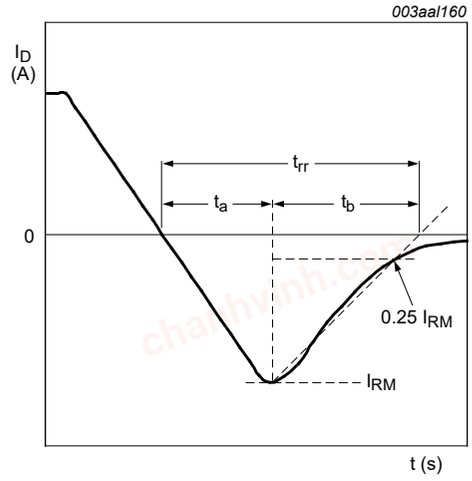


Fig. 17. Reverse recovery timing definition

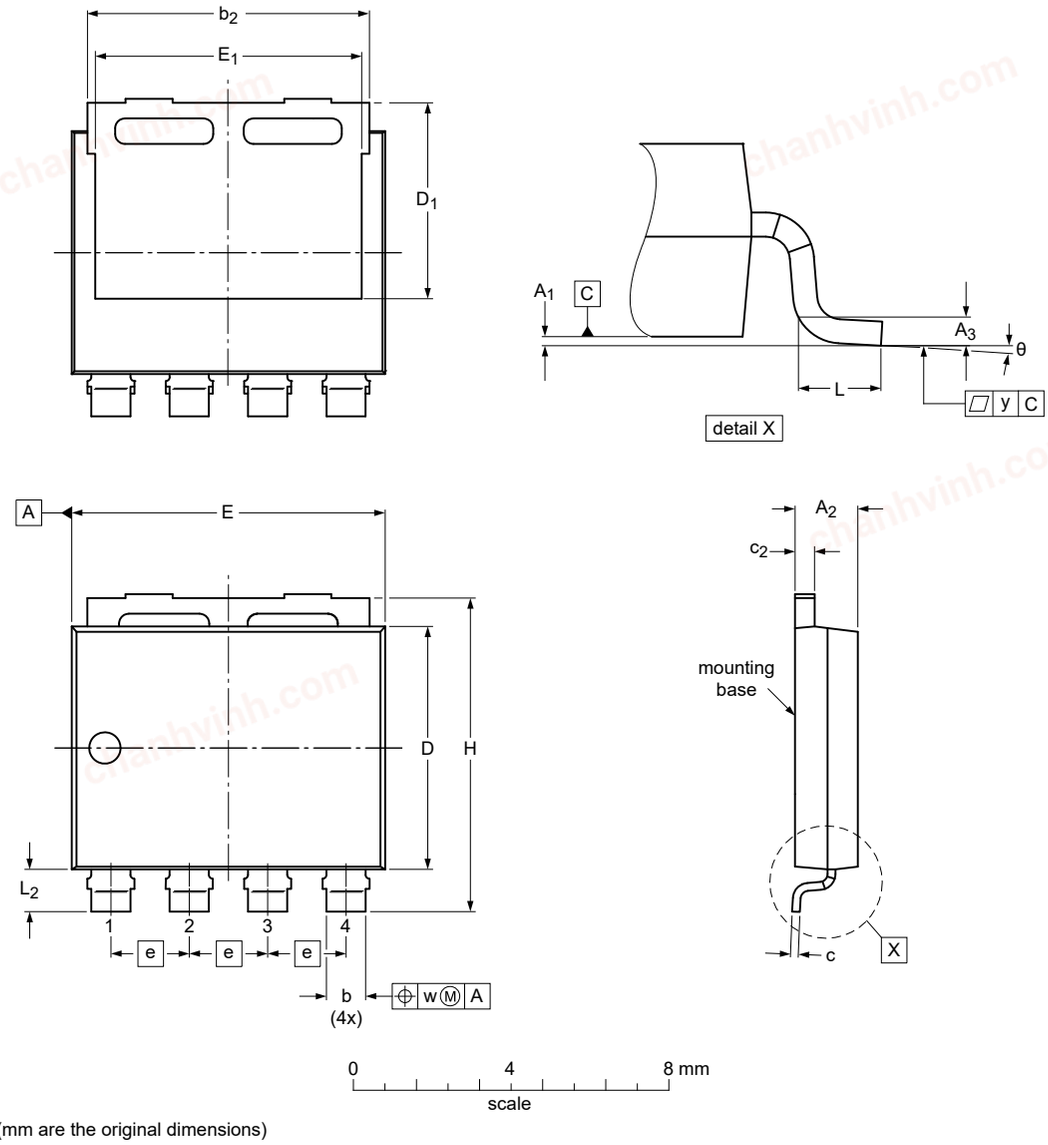
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10. Package outline

Plastic single-ended surface-mounted package (LFPAK88); 4 leads **SOT1235**



Dimensions (mm are the original dimensions)

Unit		A_1	A_2	A_3	b	b_2	c	c_2	$D^{(1)}$	$D_1^{(1)}$	$E^{(1)}$	$E_1^{(1)}$	e	$H^{(1)}$	L	L_2	w	y	θ
mm	max	0.15	1.7		1.1	7.3	0.24	0.55	6.3	5.1	8.1	6.9		8.1	0.8	1.3			8°
	nom			0.25									2.0				0.25	0.10	
	min	0.00	1.5		0.9	7.1	0.18	0.45	6.1	4.9	7.9	6.7		7.8	0.6	0.9			0°

Note
1. Plastic or metal protrusions of 0.2 mm maximum per side are not included.

sot1235_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1235						~~17-08-02~~ 17-08-07

Fig. 18. Package outline LFPAK88 (SOT1235)

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11. Soldering

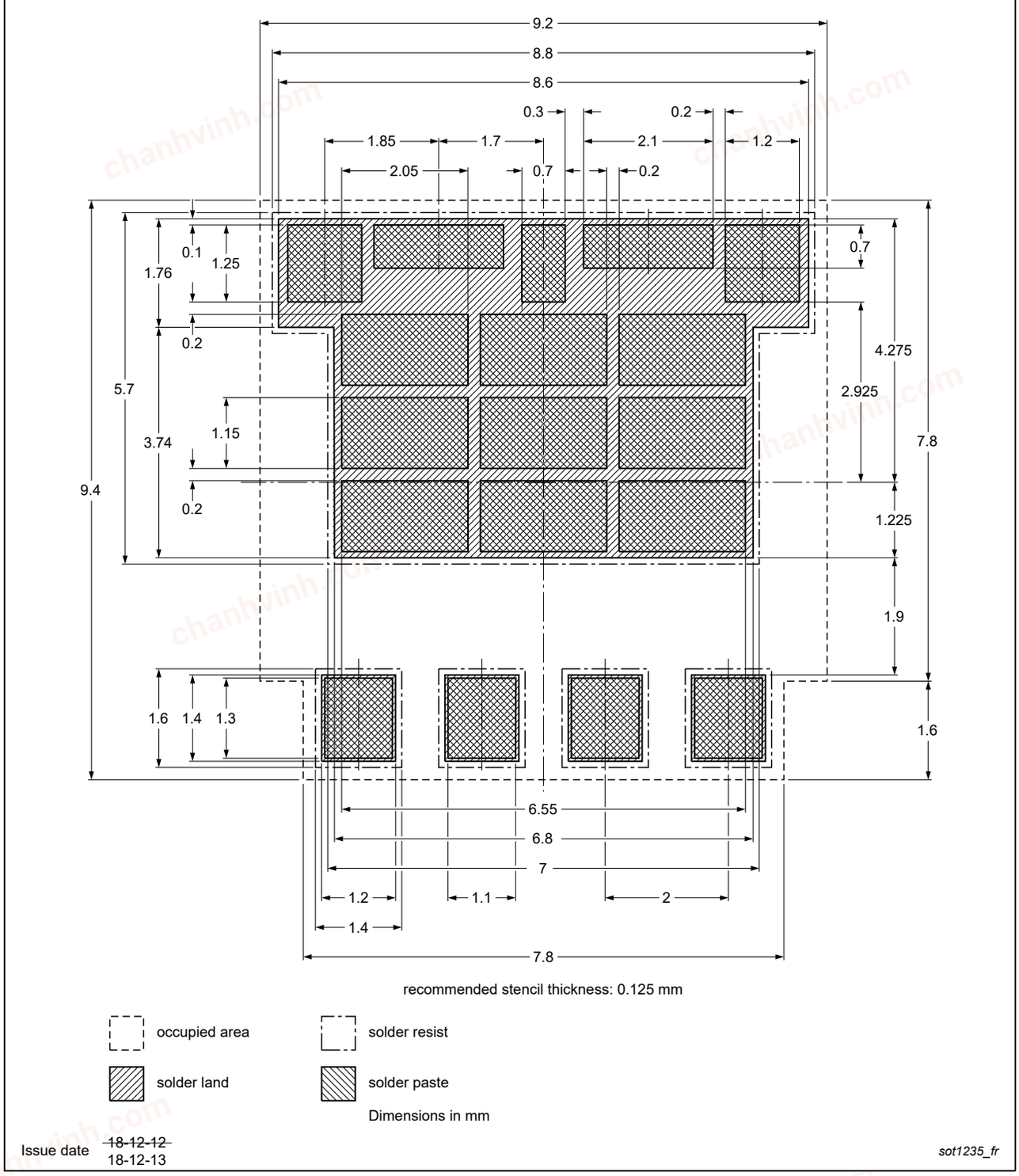


Fig. 19. Reflow soldering footprint for LFPAK88 (SOT1235)

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Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
[2] The term 'short data sheet' is explained in section "Definitions".
[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at https://www.nexperia.com.

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N-channel 40 V, 0.7 mΩ, 425 Amps continuous, standard level MOSFET in LFPAK88 using NextPowerS3 Technology

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